Features

- Trench LV MOSFET Technology
- High Speed Switching
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-CHANNEL MOSFET

Maximum Ratings

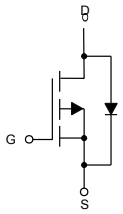
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 85°C/W Junction to Ambient (Note2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-7	A
	T_A=100°C		-4.4	
Pulsed Drain Current(Note3)		I_{DM}	-28	A
Total Power Dissipation(Note4)		P_D	1.5	W

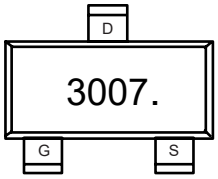
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

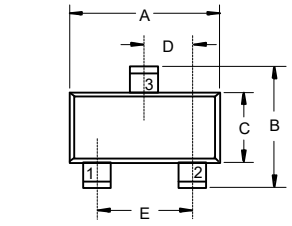
Internal Structure and Marking Code

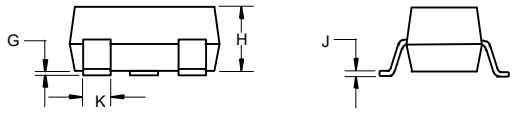


1. GATE
2. SOURCE
3. DRAIN



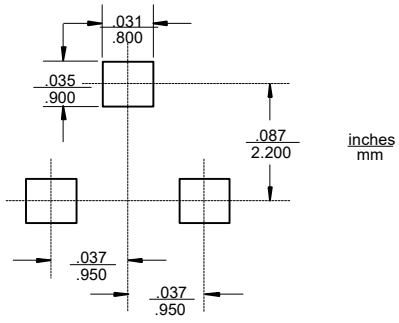
SOT-23-3L





DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.113	0.117	2.87	2.97	
B	0.108	0.112	2.75	2.85	
C	0.061	0.065	1.55	1.65	
D	0.036	0.038	0.914	0.965	
E	0.073	0.077	1.85	1.95	
G	0.0016	0.0039	0.04	0.100	
H	0.041	0.045	1.05	1.15	
J	0.006	0.007	0.14	0.17	
K	0.012	0.020	0.30	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-7A		19	25	mΩ
		V_{GS}=-4.5V, I_D=-5A		25	36	
Forward Tranconductance	g_{FS}	V_{DS}=-10V, I_D=-7A		24		S
Gate Resistance	R_g	f=1 MHz, Open drain		10		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-7	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-7A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-3.5A,di/dt=100A/μs		19		ns
Reverse Recovery Charge	Q_{rr}			7.6		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V,f=1MHz		1636		pF
Output Capacitance	C_{oss}			181		
Reverse Transfer Capacitance	C_{rss}			157		
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-10V,I_D=-7A		29		nC
Gate-Source Charge	Q_{gs}			3.6		
Gate-Drain Charge	Q_{gd}			5.1		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-15V,V_{GS}=-10V, R_G=2.5Ω, I_D=-4.2A		8		ns
Turn-On Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			58		
Turn-Off Fall Time	t_f			27		

Curve Characteristics

Fig.1 - Typical Output Characteristics

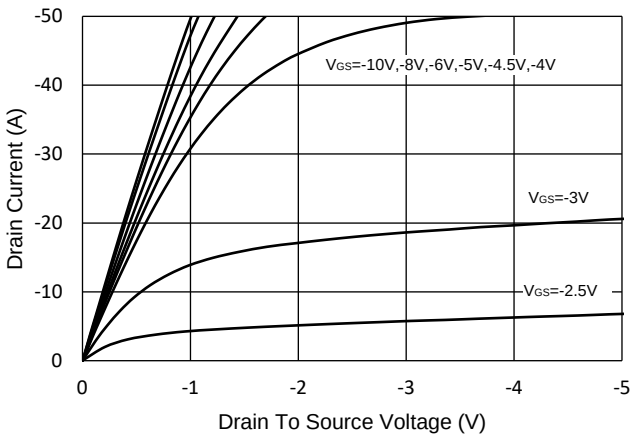


Fig.2 - Transfer Characteristic

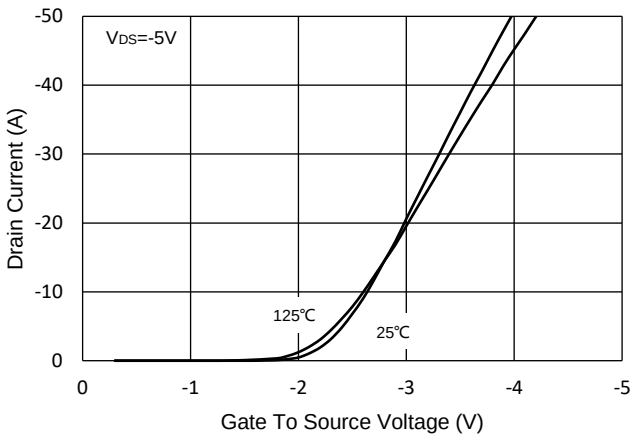


Fig.3 - $R_{DS(ON)}$ - V_{GS}

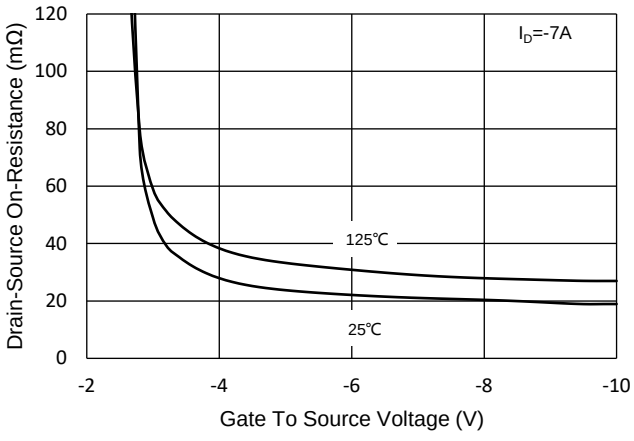


Fig.4 - $R_{DS(ON)}$ - I_D

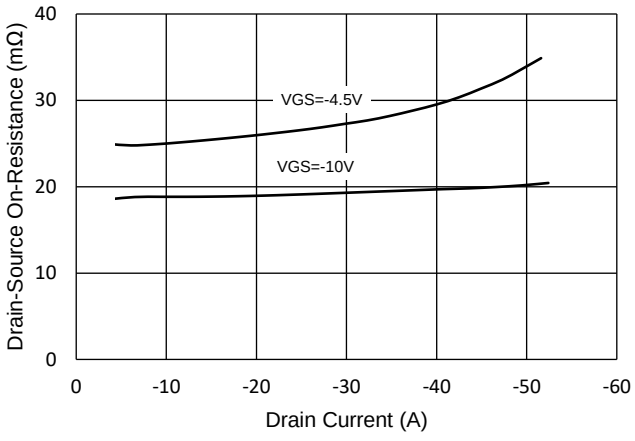


Fig.5 - Capacitance Characteristics

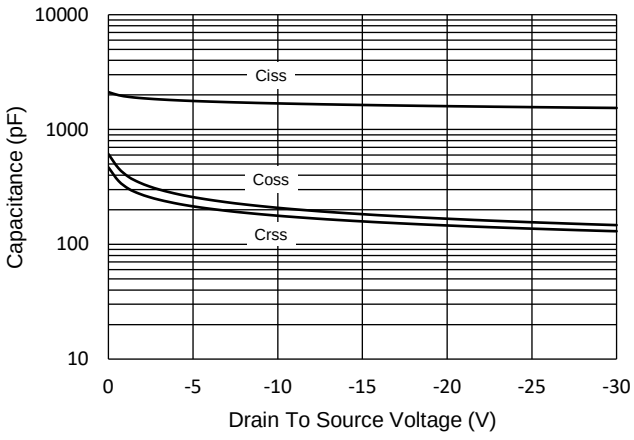
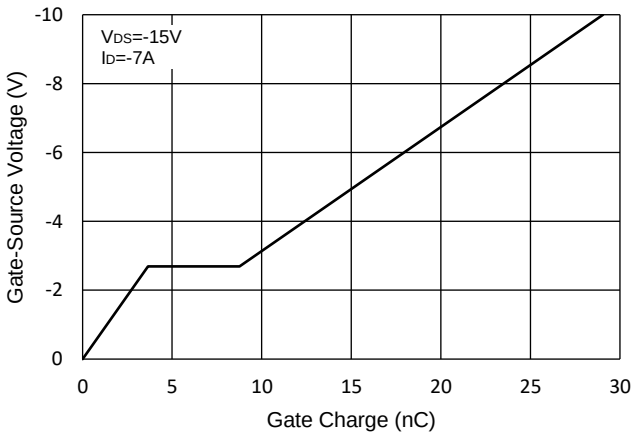


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

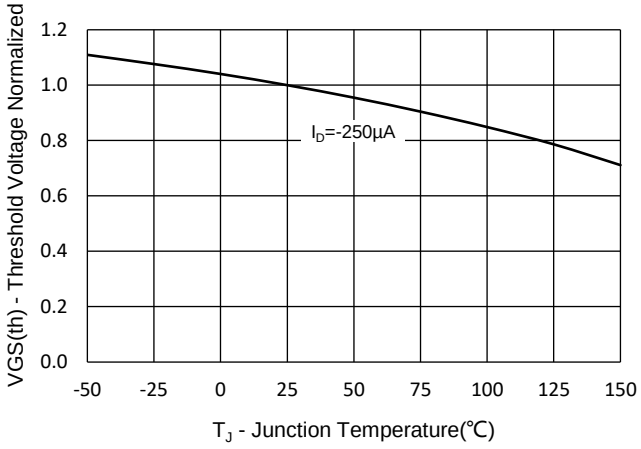


Fig.8 - Normalized On Resistance Characteristics

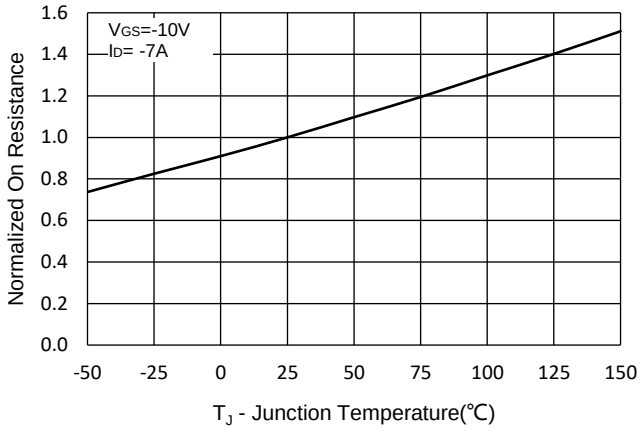


Fig.9 - I_S - V_{SD}

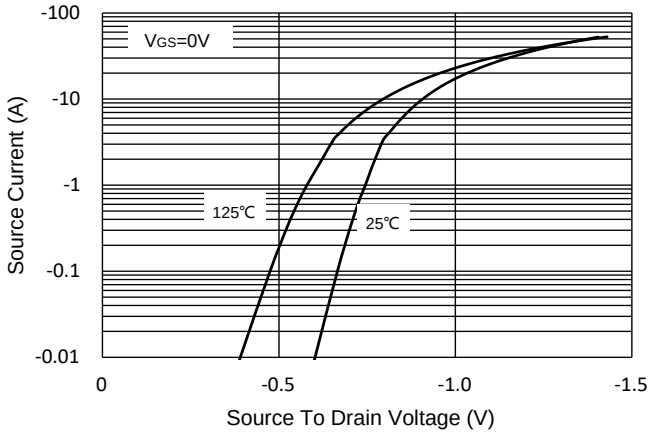


Fig.10 - Drain Current

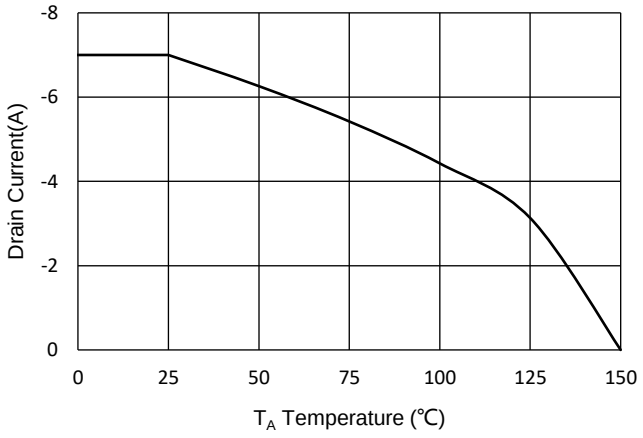
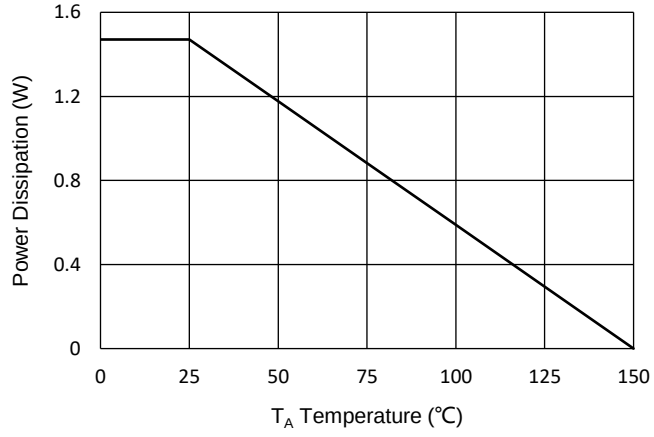


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

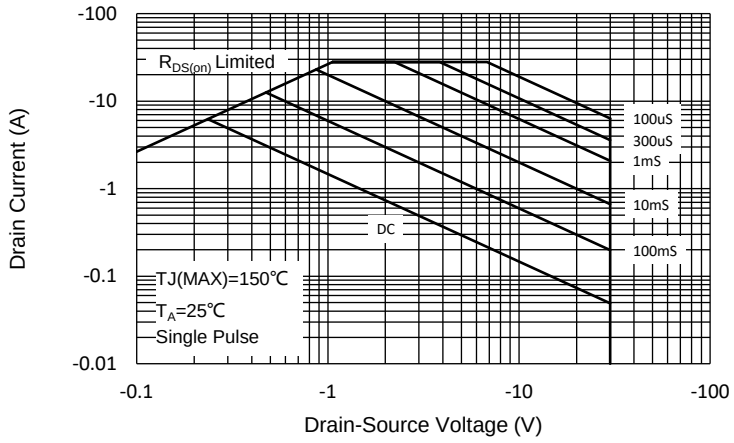
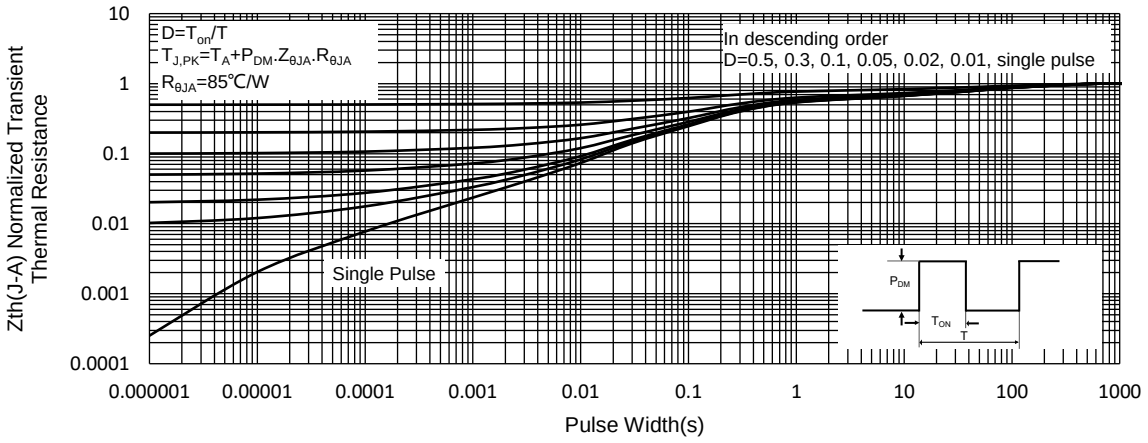


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Micro Commercial Components (MCC):

SL3007-TP